Silicon Carbide (SiC) MOSFET – 80 mohm, 1200 V, M1, TO-247-3L

NVHL080N120SC1A

- Typ. $R_{DS(on)}$ = 80 mΩ
- Ultra Low Gate Charge (typ. $Q_{G(tot)}$ = 56 nC)
- Low Effective Output Capacitance (typ. C_{oss} = 80 pF)
- 100% UIL Tested
- AEC−Q101 Qualified and PPAP Capable
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb−Free 2LI (on second level interconnection)

- Automotive On Board Charger
- Automotive DC−DC converter for EV/HEV

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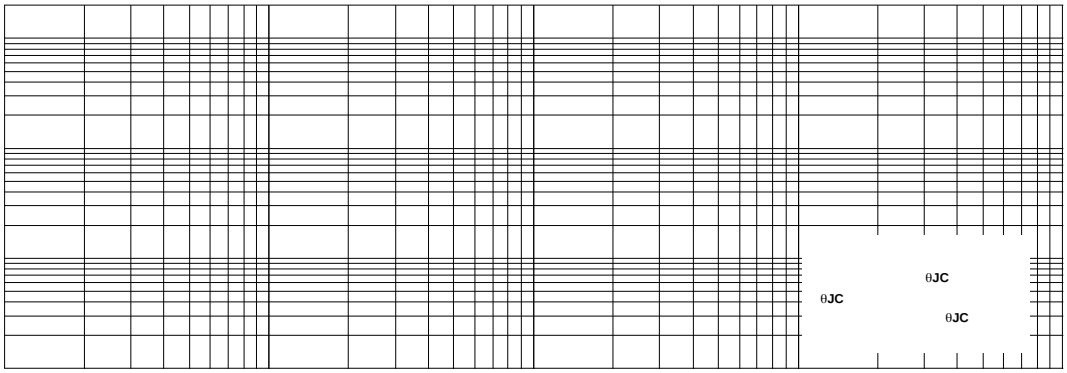
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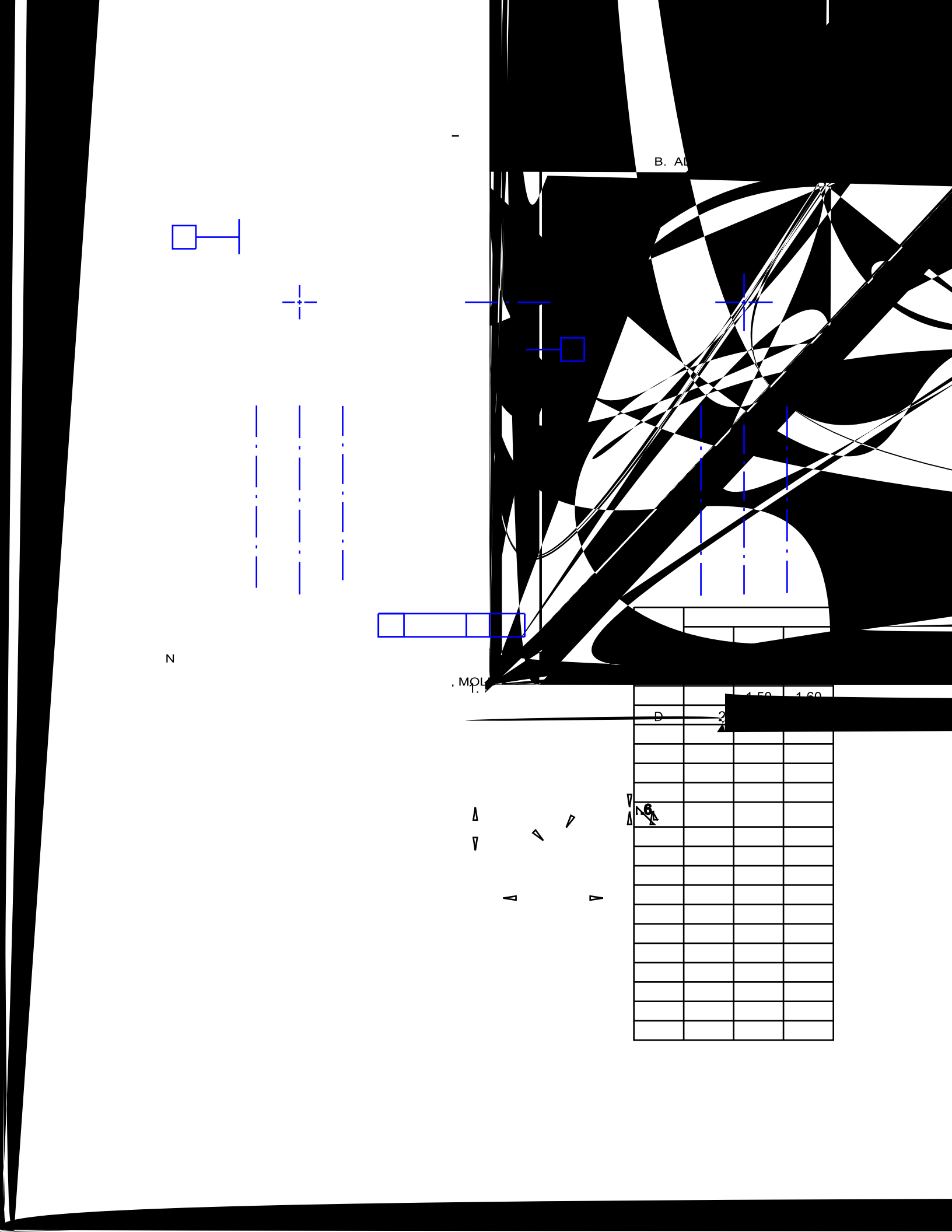
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